N-channel 60 V 2.2 mΩ standard level MOSFET in TO-220
26 October 2020 Product data sheet

## 1. General description

Standard level N-channel MOSFET in a TO-220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 2. Features and benefits

- · High efficiency due to low switching and conduction losses
- Robust construction for demanding applications
- · Standard level gate

## 3. Applications

- DC-to-DC converters
- Load switching
- Motor control
- Server power supplies

### 4. Quick reference data

#### Table 1. Quick reference data

| Symbol               | Parameter   | Conditions  |     | Min | Тур | Max | Unit |
|----------------------|---|---|-----|-----|-----|-----|------|
| V <sub>DS</sub>      | drain-source voltage                                | 25 °C ≤ T <sub>j</sub> ≤ 175 °C   |     | -   | -   | 60  | V    |
| I <sub>D</sub>       | drain current                                       | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>                                       | [1] | -   | -   | 120 | Α    |
| P <sub>tot</sub>     | total power dissipation                             | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>  |     | -   | -   | 338 | W    |
| Tj                   | junction temperature                                |   |     | -55 | -   | 175 | °C   |
| Static charact       | eristics  |   |     |     |     |     | '    |
| R <sub>DSon</sub>    | drain-source on-state resistance                    | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C;<br>Fig. 12  | [2] | -   | 1.8 | 2.2 | mΩ   |
|                      |   | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C;<br>Fig. 12; Fig. 13           |     | -   | 3   | 3.5 | mΩ   |
| Dynamic char         | acteristics   |   |     |     |     |     |      |
| $Q_{GD}$             | gate-drain charge                                   | I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V;                                |     | -   | 32  | 45  | nC   |
| Q <sub>G(tot)</sub>  | total gate charge                                   | Fig. 14; Fig. 15  |     | -   | 137 | 192 | nC   |
| Avalanche ruç        | gedness   |   | '   |     |     | ,   |      |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche<br>energy | $I_D$ = 120 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Unclamped |     | -   | -   | 913 | mJ   |

- [1] Continuous current limited by package
- [2] Measured 3 mm from package.



# 5. Pinning information

**Table 2. Pinning information** 

| Pin | Symbol | Description                       | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--------------------|----------------|
| 1   | G      | gate                              | mb                 | D              |
| 2   | D      | drain                             |                    |                |
| 3   | S      | source                            |                    | G—(F)          |
| mb  | D      | mounting base; connected to drain |                    | mbb076 S       |
|     |        |                                   |                    |                |
|     |        |                                   |                    |                |
|     |        |                                   | TO-220AB (SOT78)   |                |

# 6. Ordering information

**Table 3. Ordering information** 

| Type number  | Package | <sup>P</sup> ackage  |         |  |  |  |  |  |
|--------------|---------|--|---------|--|--|--|--|--|
|              | Name    | Description  | Version |  |  |  |  |  |
| PSMN2R0-60PS |         | plastic, single-ended package (heatsink mounted, 1 mounting hole); 3 leads; 2.54 mm pitch; 15.6 mm x 10 mm x 4.4 mm body | SOT78   |  |  |  |  |  |

# 7. Marking

**Table 4. Marking codes** 

| Type number  | Marking code    |
|--------------|-----------------|
| PSMN2R0-60PS | PSMN2R0<br>60PS |

# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                  | Conditions  |     | Min | Max  | Unit |
|---------------------|----------------------------|---|-----|-----|------|------|
| V <sub>DS</sub>     | drain-source voltage       | 25 °C ≤ T <sub>j</sub> ≤ 175 °C                                 |     | -   | 60   | V    |
| $V_{DGR}$           | drain-gate voltage         | 25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ                        |     | -   | 60   | V    |
| $V_{GS}$            | gate-source voltage        |   |     | -20 | 20   | V    |
| P <sub>tot</sub>    | total power dissipation    | T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>                          |     | -   | 338  | W    |
| I <sub>D</sub>      | drain current              | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u> | [1] | -   | 120  | А    |
|                     |                            | V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>  | [1] | -   | 120  | Α    |
| I <sub>DM</sub>     | peak drain current         | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$ ; Fig. 3   |     | -   | 1135 | А    |
| T <sub>stg</sub>    | storage temperature        |   |     | -55 | 175  | °C   |
| Tj                  | junction temperature       |   |     | -55 | 175  | °C   |
| T <sub>sld(M)</sub> | peak soldering temperature |   |     | -   | 260  | °C   |

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| Symbol               | Parameter  | Conditions  |     | Min | Max  | Unit |  |  |
|----------------------|--|---|-----|-----|------|------|--|--|
| Source-drain diode   |  |   |     |     |      |      |  |  |
| Is                   | source current                                   | T <sub>mb</sub> = 25 °C   | [1] | -   | 120  | Α    |  |  |
| I <sub>SM</sub>      | peak source current                              | pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 ^{\circ}C$  |     | -   | 1135 | Α    |  |  |
| Avalanche ruggedness |  |   |     |     |      |      |  |  |
| E <sub>DS(AL)S</sub> | non-repetitive drain-<br>source avalanche energy | $I_D$ = 120 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; Unclamped |     | -   | 913  | mJ   |  |  |

### [1] Continuous current limited by package

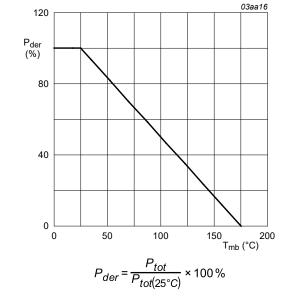
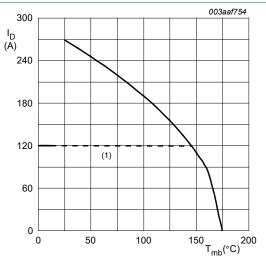
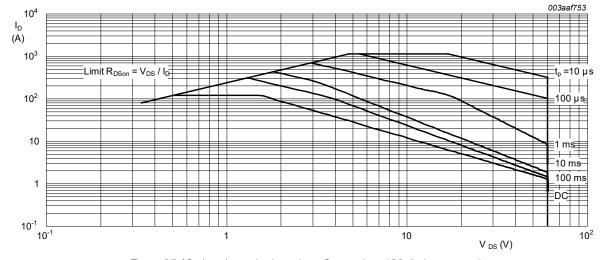


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ ; (1) Capped at 120 A due to package

Fig. 2. Continuous drain current as a function of mounting base temperature.



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse; Capped at 120 A due to package

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

| Symbol                | Parameter   | Conditions           | Min | Тур  | Max  | Unit |
|-----------------------|---|----------------------|-----|------|------|------|
| R <sub>th(j-mb)</sub> | thermal resistance from junction to mounting base | Fig. 4               | -   | 0.22 | 0.44 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance from junction to ambient       | Vertical in free air | -   | 60   | -    | K/W  |



## 10. Characteristics

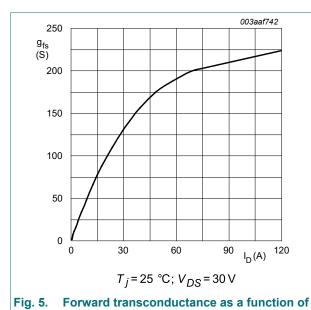
**Table 7. Characteristics** 

| Symbol               | Parameter                        | Conditions  |     | Min | Тур  | Max  | Unit |
|----------------------|----------------------------------|---|-----|-----|------|------|------|
| Static chara         | cteristics                       |   |     | '   |      |      |      |
| V <sub>(BR)DSS</sub> | drain-source                     | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C                     |     | 54  | -    | -    | V    |
|                      | breakdown voltage                | I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                      |     | 60  | -    | -    | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$<br>Fig. 10                     |     | 1   | -    | -    | V    |
|                      |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 10; Fig. 11$                |     | 2   | 3    | 4    | V    |
|                      |                                  | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 10$                        |     | -   | -    | 4.6  | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C                       |     | -   | 0.03 | 10   | μΑ   |
|                      |                                  | V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C                      |     | -   | -    | 1000 | μΑ   |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                      |     | -   | -    | 100  | nA   |
|                      |                                  | V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C                       |     | -   | -    | 100  | nA   |
| R <sub>DSon</sub>    | drain-source on-state resistance | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C;<br>Fig. 12                                    | [1] | -   | 1.8  | 2.2  | mΩ   |
|                      |                                  | $V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C;<br>Fig. 12; Fig. 13                          |     | -   | 4.3  | 5.1  | mΩ   |
|                      |                                  | V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 100 °C;<br>Fig. 12; Fig. 13 |     | -   | 3    | 3.5  | mΩ   |

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| Symbol                 | Parameter                             | Conditions   | Min  | Тур  | Max   | Unit |
|------------------------|---------------------------------------|--|------|------|-------|------|
| R <sub>G</sub>         | gate resistance                       | f = 1 MHz  | 0.45 | 0.9  | 1.8   | Ω    |
| Dynamic ch             | aracteristics                         |  |      | '    |       |      |
| $Q_{G(tot)}$           | total gate charge                     | I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V;<br>Fig. 14; Fig. 15               | -    | 137  | 192   | nC   |
|                        |                                       | $I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; \frac{\text{Fig. 14}}{\text{Fig. 15}};$ | -    | 129  | 181   | nC   |
| Q <sub>GS</sub>        | gate-source charge                    | I <sub>D</sub> = 75 A; V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 10 V;                                   | -    | 48   | 68    | nC   |
| Q <sub>GS(th)</sub>    | pre-threshold gate-<br>source charge  | Fig. 14; Fig. 15   | -    | 29   | -     | nC   |
| Q <sub>GS(th-pl)</sub> | post-threshold gate-<br>source charge |  | -    | 19   | -     | nC   |
| Q <sub>GD</sub>        | gate-drain charge                     |  | -    | 32   | 45    | nC   |
| V <sub>GS(pl)</sub>    | gate-source plateau<br>voltage        | V <sub>DS</sub> = 30 V; <u>Fig. 14</u> ; <u>Fig. 15</u>  | -    | 5.7  | -     | V    |
| C <sub>iss</sub>       | input capacitance                     | V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; f = 1 MHz;  | -    | 9997 | 13500 | pF   |
| C <sub>oss</sub>       | output capacitance                    | T <sub>j</sub> = 25 °C; <u>Fig. 16</u>   | -    | 1210 | 1640  | pF   |
| C <sub>rss</sub>       | reverse transfer capacitance          |  | -    | 594  | 835   | pF   |
| t <sub>d(on)</sub>     | turn-on delay time                    | $V_{DS} = 30 \text{ V}; R_L = 0.4 \Omega; V_{GS} = 10 \text{ V};$  | -    | 42   | 63    | ns   |
| t <sub>r</sub>         | rise time                             | $R_{G(ext)} = 4.7 \Omega$  | -    | 56   | 84    | ns   |
| t <sub>d(off)</sub>    | turn-off delay time                   |  | -    | 115  | 173   | ns   |
| t <sub>f</sub>         | fall time                             | 1  | -    | 49   | 74    | ns   |
| Source-drai            | in diode                              | •  | 1    |      | 1     |      |
| V <sub>SD</sub>        | source-drain voltage                  | $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$                           | -    | 0.8  | 1.2   | V    |
| t <sub>rr</sub>        | reverse recovery time                 | $I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$                        | -    | 57   | 75    | ns   |
| Q <sub>r</sub>         | recovered charge                      | V <sub>DS</sub> = 30 V   | -    | 80   | 104   | nC   |
|                        | 1                                     | 1  |      |      |       |      |

### [1] Measured 3 mm from package.



drain current; typical values

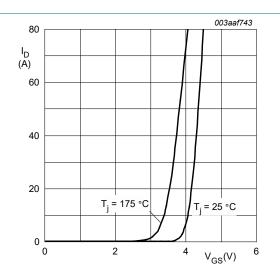


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

#### N-channel 60 V 2.2 m $\Omega$ standard level MOSFET in TO-220

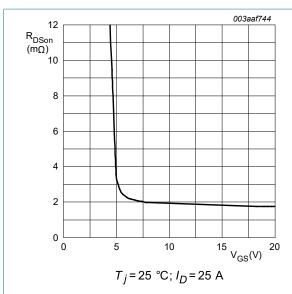


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

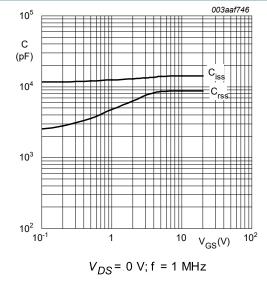


Fig. 8. Input and reverse transfer capacitances as a function of gate-source voltage, typical values

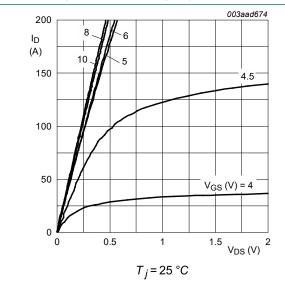


Fig. 9. Output characteristics: drain current as a function of drain-source voltage; typical values

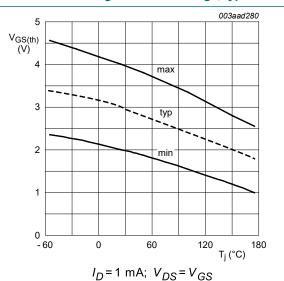


Fig. 10. Gate-source threshold voltage as a function of junction temperature

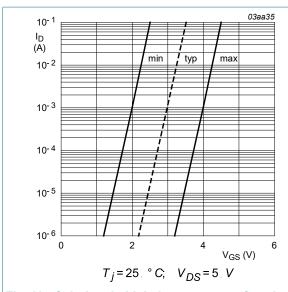


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

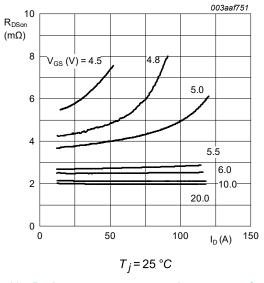
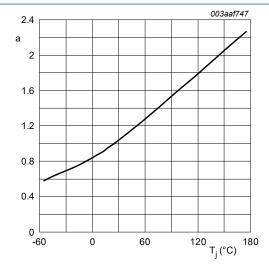


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values



 $T_j = 25 \text{ °C}; I_D = 25 \text{ A}$ 

Fig. 13. Drain-source on-state resistance as a function of gate-source voltage; typical values

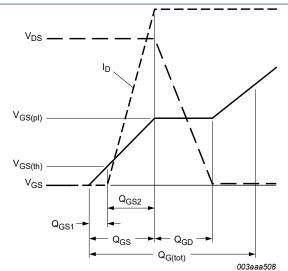


Fig. 14. Gate charge waveform definitions

#### N-channel 60 V 2.2 m $\Omega$ standard level MOSFET in TO-220

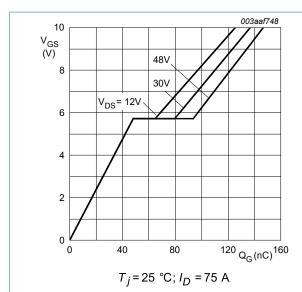


Fig. 15. Gate-source voltage as a function of gate charge; typical values

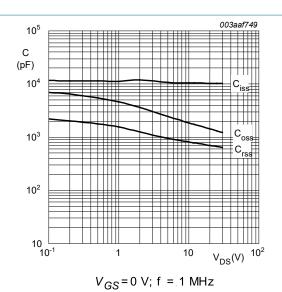


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

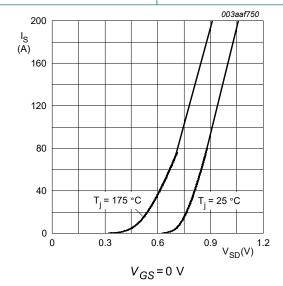
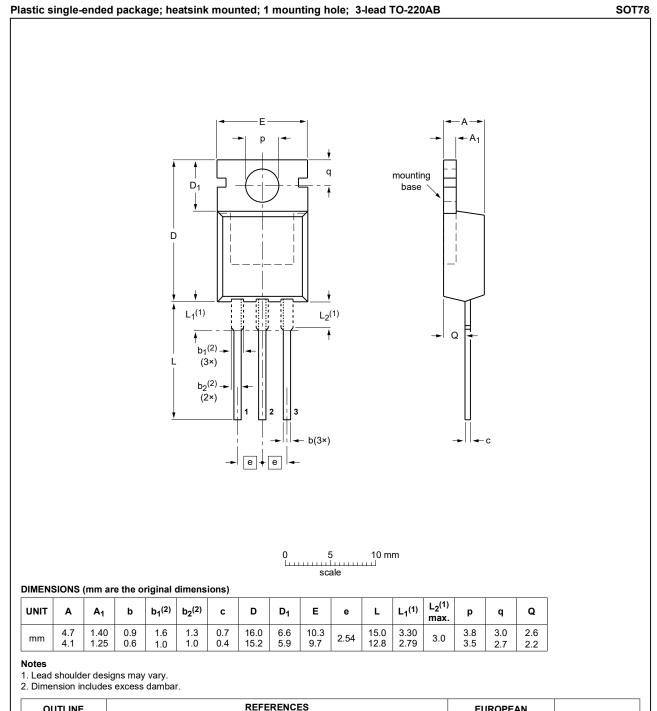


Fig. 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

# 11. Package outline



| OUTLINE |     | REFER           | EUROPEAN | ISSUE DATE |            |                                 |
|---------|-----|-----------------|----------|------------|------------|---------------------------------|
| VERSION | IEC | JEDEC           | JEITA    |            | PROJECTION | ISSUE DATE                      |
| SOT78   |     | 3-lead TO-220AB | SC-46    |            |            | <del>08-04-23</del><br>08-06-13 |

Fig. 18. Package outline TO-220AB (SOT78)

#### N-channel 60 V 2.2 mΩ standard level MOSFET in TO-220

## 12. Legal information

#### **Data sheet status**

| Document status [1][2]         | Product<br>status [3] | Definition  |
|--------------------------------|-----------------------|---|
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| Preliminary [short] data sheet | Qualification         | This document contains data from the preliminary specification.                       |
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